2SD2479

Silicon NPN epitaxial planar type

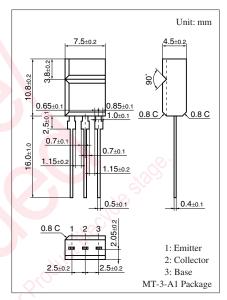
For low-frequency amplification

■ Features

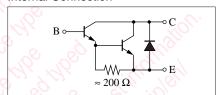
- High forward current transfer ratio h_{FE}
- Allowing supply with the radial taping

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	120	V	
Collector-emitter voltage (Base open)	V _{CEO}	100	V	
Emitter-base voltage (Collector open)	V_{EBO}	5	V	
Collector current	I_{C}	2	A	
Peak collector current	I_{CP}	3	A	
Collector power dissipation	P_{C}	1.5	W	
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	



Internal Connection



■ Electrical Characteristics $T_a = 25$ °C ± 3°C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_C = 100 \mu\text{A}, I_E = 0$	120			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	100	J.		V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 100 \mu A, I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 25 \text{ V}, I_{E} = 0$			0.1	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 4 \text{ V}, I_C = 0$			1	μΑ
Forward current transfer ratio *1, 2	h_{FE}	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ A}$	4 000		40 000	_
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_C = 1 \text{ A}, I_B = 1 \text{ mA}$			1.5	V
Base-emitter saturation voltage *1	V _{BE(sat)}	$I_C = 1 \text{ A}, I_B = 1 \text{ mA}$			2	V
Transition frequency	f_T	$V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		150		MHz

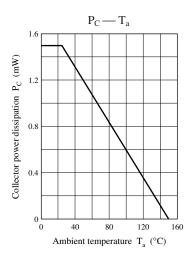
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

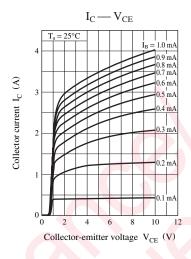
2. *1: Pulse measurement

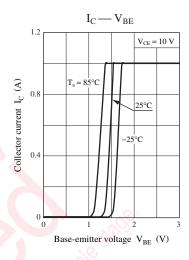
*2: Rank classification

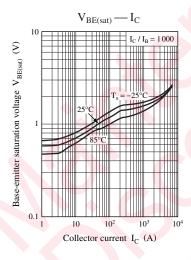
Rank	Q	R	S	
h_{FE}	4000 to 10000	8 000 to 20 000	16 000 to 40 000	

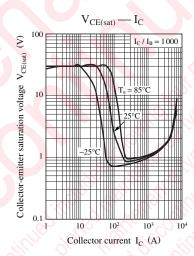
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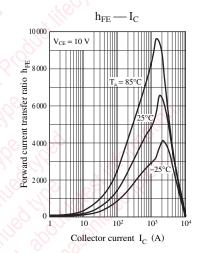


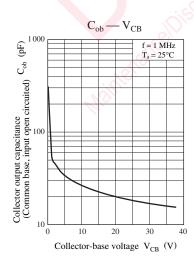












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